Silicon Carbide Schottky Diode

650 V, 10 A

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

ABSOLUTE MAXIMUM RATINGS

(T_C = 25°C, Unless otherwise specified)

Symbol	Parar	FF- SP1065B-F085	Unit		
V _{RRM}	Peak Repetitive Rev	verse Voltage	650	V	
E _{AS}	Single Pulse Avalan	che Energy (Note 1)	49	mJ	
١ _F	Continuous Rectified @ $T_C < 139^{\circ}C$	10	A		
	Continuous Rectified @ T _C < 135°C	11			
I _{F, Max}	Non–Repetitive Peak Forward	$T_C = 25^{\circ}C$, 10 µs	650	A	
	Surge Current	$T_{C} = 150^{\circ}C, 10 \ \mu s$	570		
I _{F, SM}	Non–Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	45	A	
P _{tot}	Power Dissipation	$T_C = 25^{\circ}C$	75	W	
		T _C = 150°C	12.5		
T _J , T _{STG}	T _J , T _{STG} Operating and Storage Temperature Range			°C	

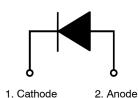
1. E_{AS} of 49 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 14 A, V = 50 V.



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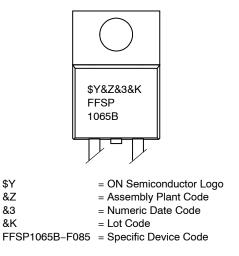
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ELECTRICAL CONNECTION





MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.0	°C/W	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP1065B-F085	FFSP1065B	TO220	Tube	N/A	N/A	50 Units

ELECTRICAL CHARACTERISTICS $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25°C	-	1.38	1.7	V
		I _F = 10 A, T _C = 125°C	-	1.6	2.0	
		I _F = 10 A, T _C = 175°C	-	1.72	2.4	
I _R	Reverse Current	$V_{R} = 650 \text{ V}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	0.5	40	μΑ
		V _R = 650 V, T _C = 125°C	-	1.0	80	
		V _R = 650 V, T _C = 175°C	-	2.0	160	
Q _C	Total Capacitive Charge	V = 400 V	-	25	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	421	-	pF
		V _R = 200 V, f = 100 kHz	-	46	-	
		V _R = 400 V, f = 100 kHz	-	35	-	1

TYPICAL CHARACTERISTICS $T_J = 25^{\circ}C$ Unless Otherwise Noted

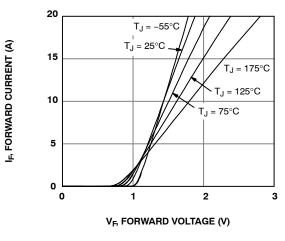


Figure 1. Forward Characteristics

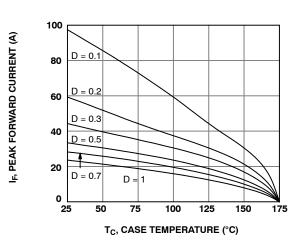
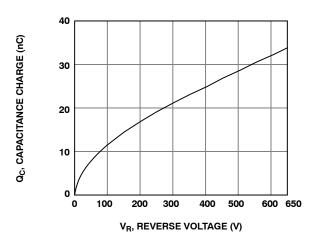


Figure 3. Current Derating





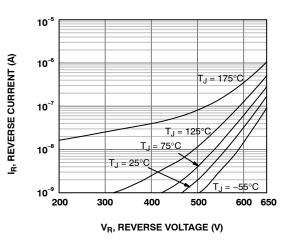


Figure 2. Reverse Characteristics

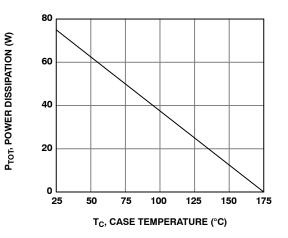
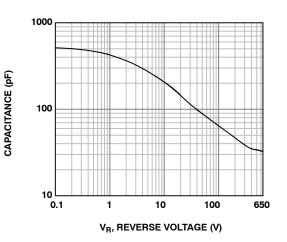
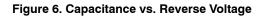
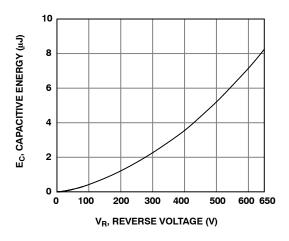


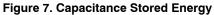
Figure 4. Power Dissipation

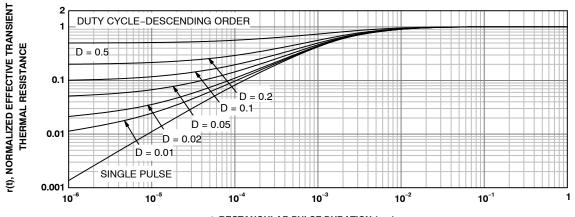




TYPICAL CHARACTERISTICS T_J = 25°C Unless Otherwise Noted (continued)

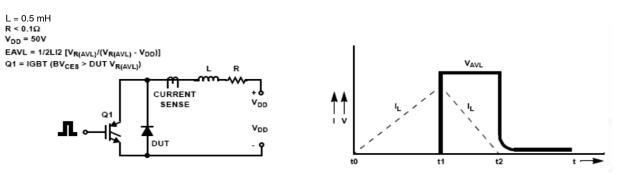






t, RECTANGULAR PULSE DURATION (sec)

Figure 8. Junction-to-Case Transient Thermal Response Curve



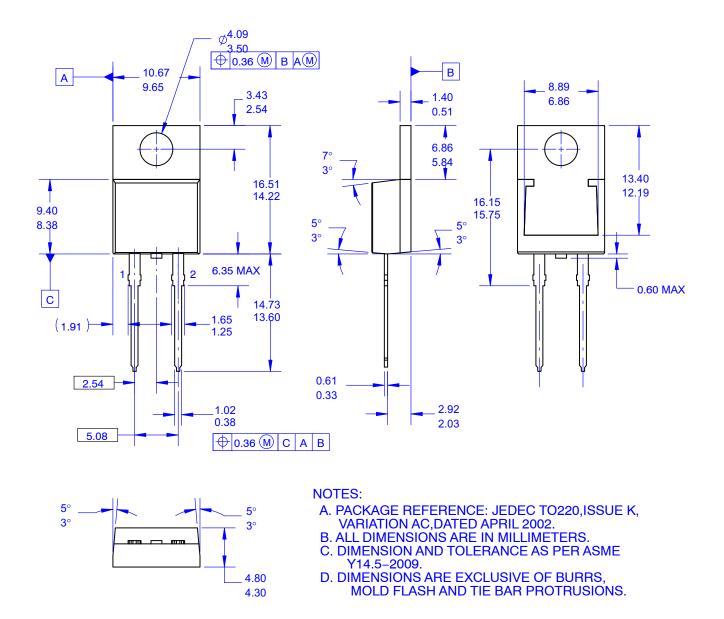
TEST CIRCUIT AND WAVEFORMS

Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



TO-220-2LD CASE 340BB ISSUE O

DATE 31 AUG 2016



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